

Features

- Ultra-Small Surface Mount Package
- Halogen Free. "Green" Device (Note 1)
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings @ 25°C Unless Otherwise Specified

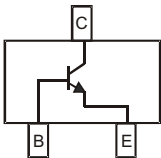
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	75	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Maximum Collector Current	I_{CM}	0.6	A
Collector Power Dissipation	P_C	200	mW

Note: 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

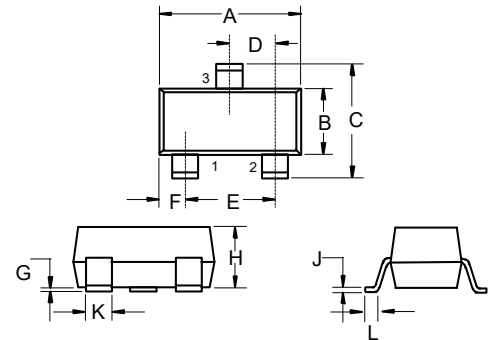
Marking: K3P

Internal Structure



NPN Plastic Encapsulate Transistors

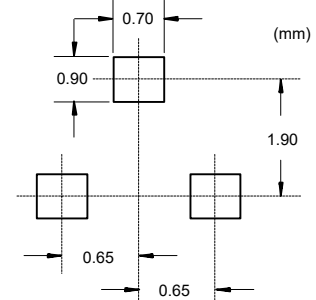
SOT-323



DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.071	0.087	1.80	2.20	
B	0.045	0.053	1.15	1.35	
C	0.083	0.096	2.10	2.45	
D	0.026		0.65		TYP.
E	0.047	0.055	1.20	1.40	
F	0.012	0.016	0.30	0.40	
G	0.000	0.004	0.00	0.10	
H	0.035	0.044	0.90	1.10	
J	0.002	0.010	0.05	0.25	
K	0.006	0.016	0.15	0.40	
L	0.010	0.018	0.26	0.46	

Suggested Solder Pad Layout



Electrical Characteristics @ 25°C Unless Otherwise Specified

Parameter	Symbol	Min	Typ	Max	Units	Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	75			V	$I_C=10\mu A, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40			V	$I_C=10mA, I_B=0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6			V	$I_E=10\mu A, I_C=0$
Collector-Base Cutoff Current	I_{CBO}			100	nA	$V_{CB}=70V, I_E=0$
Collector Cutoff Current	I_{CEX}			10	nA	$V_{CE}=60V, V_{BE}=3V$
Emitter Cutoff Current	I_{EBO}			100	nA	$V_{EB}=3V, I_C=0$
DC Current Gain (Note2)	h_{FE1}	50				$V_{CE}=10V, I_C=1mA$
	h_{FE2}	100		300		$V_{CE}=10V, I_C=150mA$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.6	V	$I_C=500mA, I_B=50mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	0.6		1.2	V	$I_C=500mA, I_B=50mA$
Transition Frequency	f_T	300			MHz	$V_{CE}=20V, I_C=20mA, f=100MHz$
Output Capacitance	C_{ob}			8	pF	$V_{CB}=10V, I_E=0, f=1MHz,$
Delay Time	t_d			10	ns	$V_{CC}=30V, V_{BE(off)}=0.5V$
Rise Time	t_r			25	ns	$I_C=150mA, I_{B1}=15mA$
Storage Time	t_s			225	ns	$V_{CC}=30V, I_C=150mA$
Fall Time	t_f			60	ns	$I_{B1}=I_{B2}=15mA$

 Note: 2.Pluse Width $\leq 300\mu s$, Duty Cycle $\leq 2.0\%$

Curve Characteristics

Fig. 1 - Static Characteristics

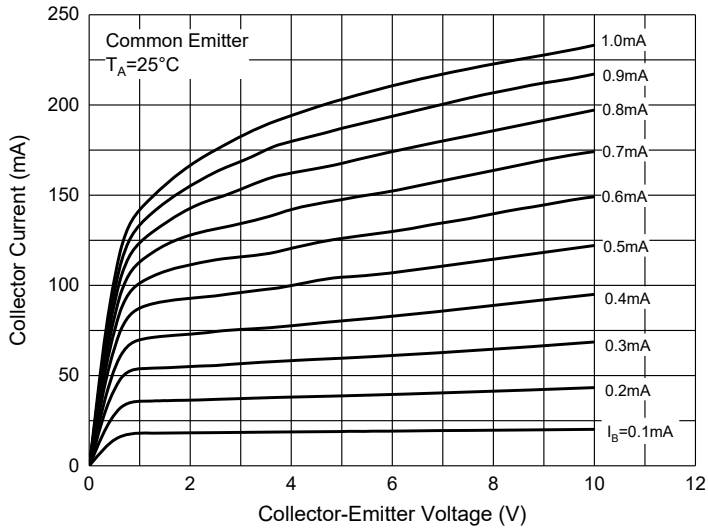


Fig. 2 - DC Current Gain Characteristics

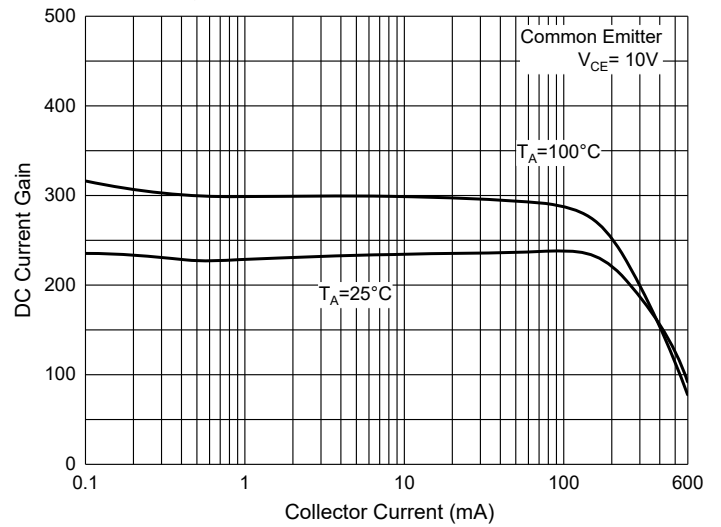


Fig. 3 - Collector-Emitter Saturation Voltage Characteristics

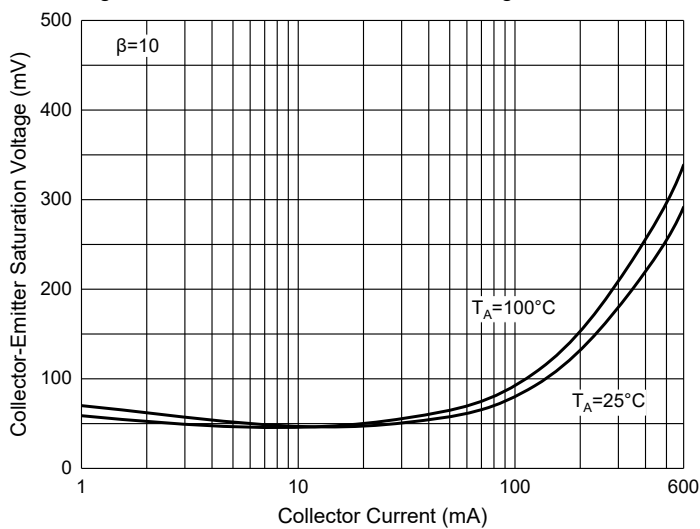


Fig. 4 - Base-Emitter Saturation Voltage Characteristics

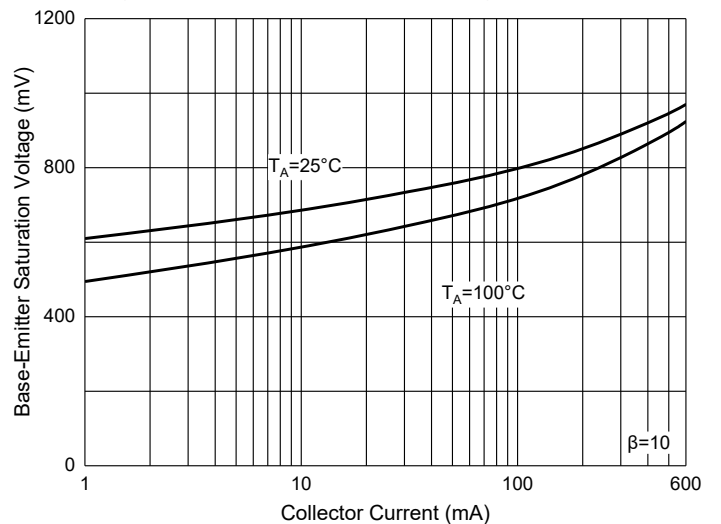


Fig. 5 - Base-Emitter Voltage Characteristics

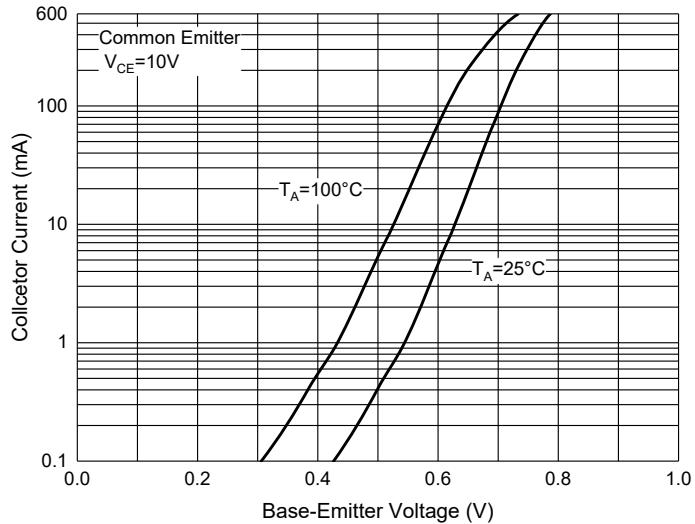


Fig. 6 - Collector Power Derating Curve

